



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	l _D max T _A = 25°C		
60V	3Ω @ V _{GS} = 10V	300mA		

Description and Applications

This MOSFET has been designed to minimize the on-state resistance $(R_{DS(on)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor control
- Power Management Functions

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
 Lead, Halogen and Antimony Free, RoHS Compliant "Green" Device (Notes 1, 2 and 3)
- Qualified to AEC-Q101 Standards for High Reliability

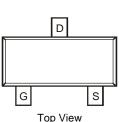
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Alloy 42 leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Weight: 0.008 grams (approximate

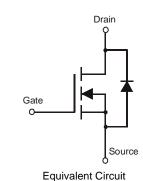


SOT23

Top View



Top View Pin Out Configuration



Ordering Information (Note 4)

Part Number	Case	Packaging
2N7002E-7-F	SOT23	3000/Tape & Reel

Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. No purposely added lead. Halogen and Antimony free

Υ

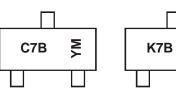
Shanghai A/T Site

2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com.

3. Product manufactured with Date Code V12 (week 50, 2008) and newer are built with Green Molding Compound. Product manufactured prior to Date Code V12 are built with Non-Green Molding Compound and may contain Halogens or Sb₂O₃ Fire Retardants

4. For packaging details, go to our website at http://www.diodes.com.

Marking Information



Chengdu A/T Site

 $K = SAT (Shanghai Assembly/ Test site) \\ C = CAT (Chengdu Assembly/ Test site) \\ 7B= Product Type Marking Code \\ YM = Date Code Marking \\ Y = Year (ex: N = 2002) \\ M = Month (ex: 9 = September)$

Date Code Key

Date Coue N	ey														
Year	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017
Code	Р	R	S	Т	U	V	W	Х	Y	Z	A	В	С	D	E
Month	lan	Ба	h	Mar	A	Mav	1	-	1	A	San	0		lav	Dee
Wonth	Jan	Fe	a	war	Apr	way	Ju	n	Jul	Aug	Sep	Oc	τι	Vov	Dec
Code	1	2		3	4	5	6		7	8	9	0		Ν	D



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Units	
Drain-Source Voltage		V _{DSS}	60	V	
Drain-Gate Voltage $R_{GS} \le 1.0M\Omega$			V _{DGR}	60	V
Gate-Source Voltage	_	Continuous Pulsed	V _{GSS}	±20 ±40	V
Continuous Drain Current (Note 5) V _{GS} = 10V	Steady State	T _A = 25°C T _A = 70°C	ID	250 200	mA
Continuous Drain Current (Note 6) $V_{GS} = 10V$ Steady State $T_A = 25^{\circ}C$ $T_A = 70^{\circ}C$			Ι _D	300 240	mA
Maximum Body Diode Forward Current (Note 6)		Is	500	mA	
Pulsed Drain Current (10µs pulse, duty cycle = 1%	6)	I _{DM}	800	mA	

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Units	
Total Power Dissipation	(Note 5)	D	370	mW	
	(Note 6)	PD	540	IIIVV	
Thermal Resistance, Junction to Ambient	(Note 5)	D	348		
	(Note 6)	$R_{ extsf{ heta}JA}$	241	°C/W	
Thermal Resistance, Junction to Case	(Note 6)	R _θ JC	91		
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to 150	°C	

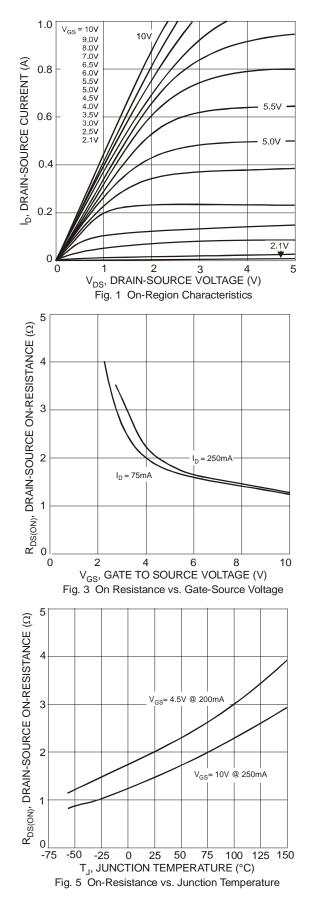
Electrical Characteristics @T_A = 25°C unless otherwise specified

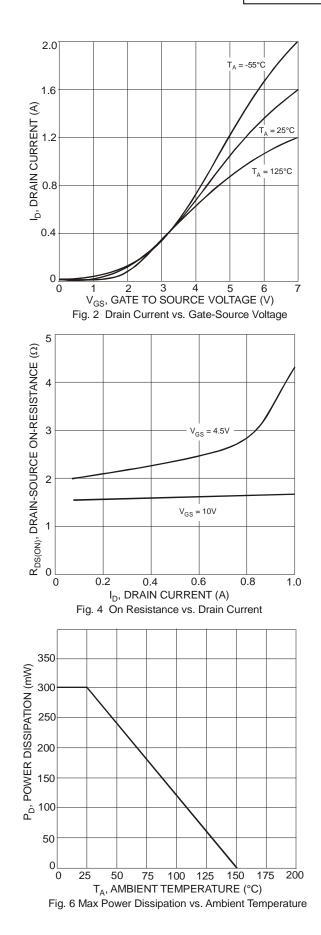
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						•
Drain-Source Breakdown Voltage	BV _{DSS}	60	70		V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	I _{DSS}		_	1.0 500	μA	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Body Leakage	IGSS	_	_	±10	nA	$V_{GS} = \pm 15V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						·
Gate Threshold Voltage	V _{GS(th)}	1.0		2.5	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance @ T _J = 25°C	R _{DS (ON)}	_	1.6 2.0	3 4	Ω	$V_{GS} = 10V, I_D = 250mA$ $V_{GS} = 4.5V, I_D = 200mA$
On-State Drain Current	I _{D(ON)}	0.8	1.0		Α	V _{GS} = 10V, V _{DS} = 7.5V
Forward Transconductance	g fs	80	_		mS	$V_{DS} = 10V, I_D = 0.2A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss	_	22	50	pF	
Output Capacitance		_	11	25	pF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$
Reverse Transfer Capacitance	C _{rss}		2.0	5.0	pF	
Gate resistance	Rq		120		Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge (V _{GS} = 4.5V)	Qq		223		рС	
Gate-Source Charge	Q _{gs}	_	82		рС	V _{DS} = 10V, I _D = 250mA
Gate-Drain Charge	Q _{gd}	_	178		рС	1
SWITCHING CHARACTERISTICS (Note 8)						
Turn-On Delay Time	t _{D(ON)}	_	7.0	20	ns	$V_{DD} = 30V, I_D = 0.2A,$
Turn-Off Delay Time	t _{D(OFF)}		11	20	ns	$R_L = 150\Omega$, $V_{GEN} = 10V$, $R_{GEN} = 25\Omega$

Notes:

Device mounted on FR-4 PCB, with minimum recommended pad layout
 Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.

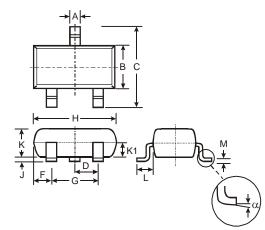






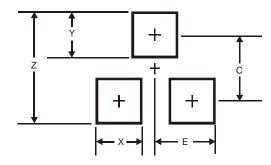


Package Outline Dimensions



SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
Κ	0.903	1.10	1.00				
K1	-	-	0.400				
L	0.45	0.61	0.55				
М	0.085	0.18	0.11				
α	0°	8°	-				
All	Dimens	ions in	mm				

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35



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